

/ Descriptions

SOP-8 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features

$V_{DS}=30V$

$I_D=13A$ ($V_{GS} = 10V$)

$R_{DS(ON)}<11.5m$ ($V_{GS}=10V$)

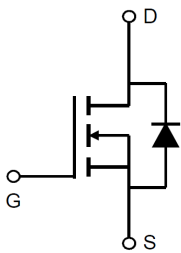
$R_{DS(ON)}<15.5m$ ($V_{GS}=4.5V$)

Halogen-free Product.

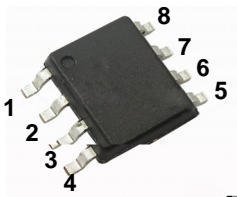
/ Applications

This device is suitable for high side switch in SMPS and general purpose applications.

/ Equivalent Circuit



/ Pinning



PIN1 S PIN 2 S PIN 3 S PIN4 G

PIN 5 D PIN 6 D PIN 7 D PIN 8 D

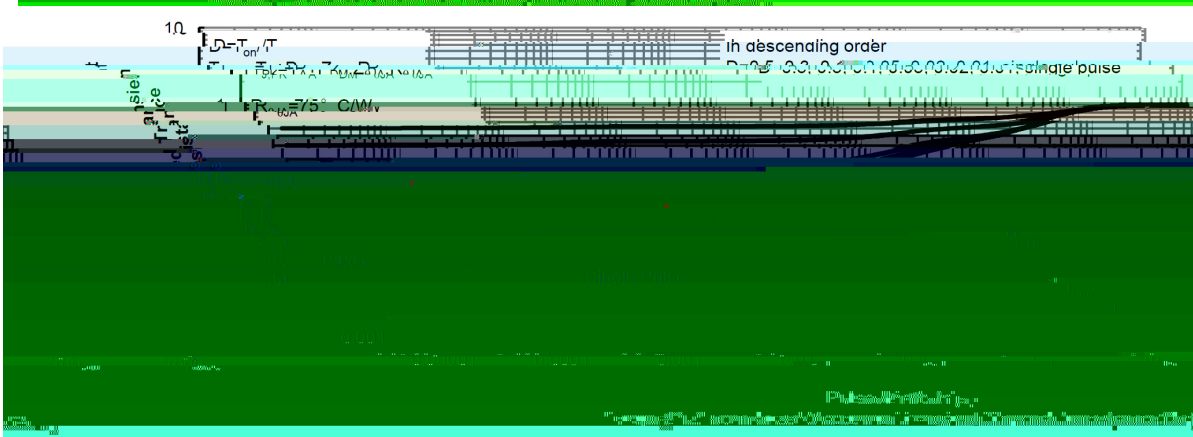
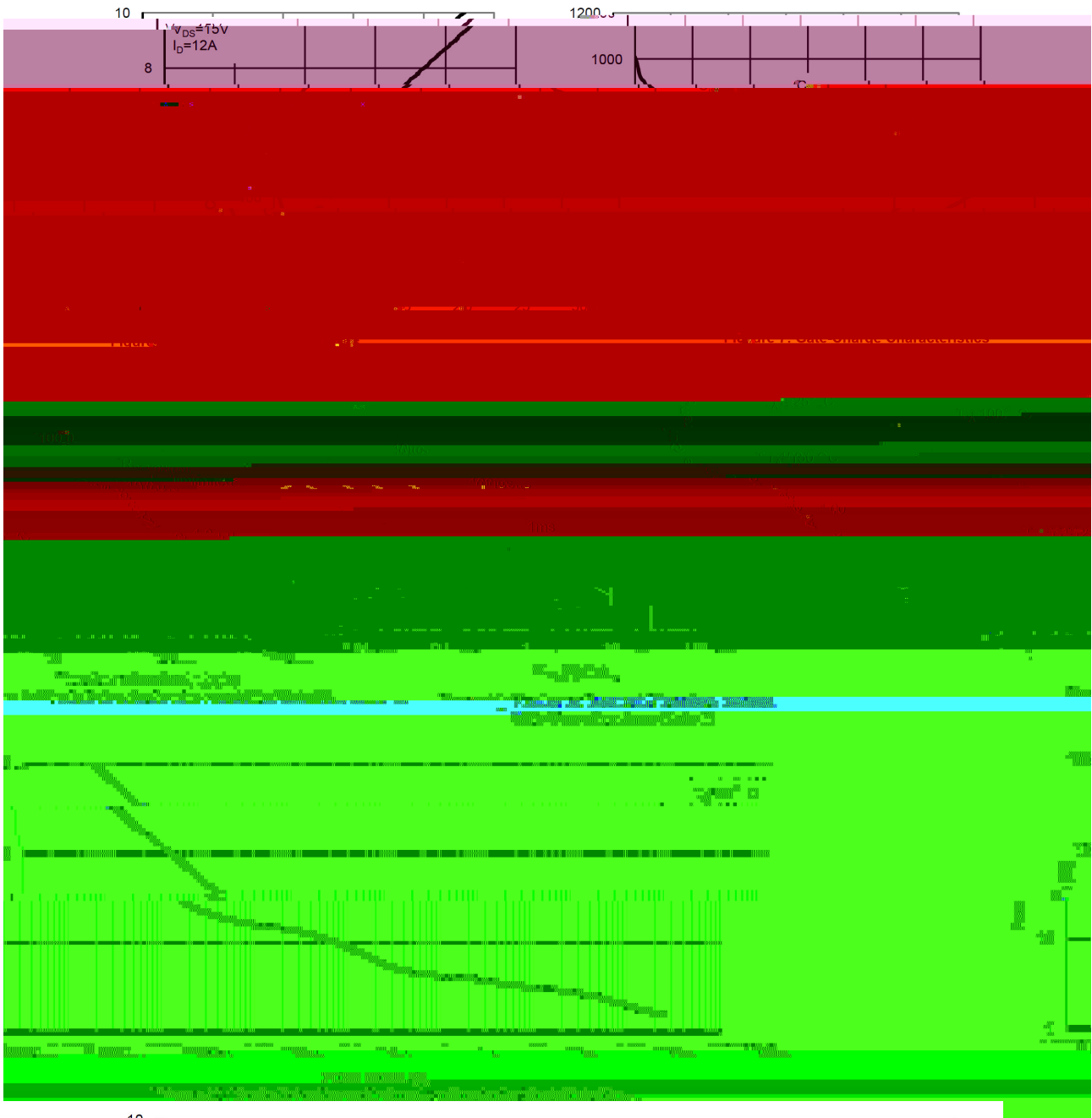
/ h_{FE} Classifications & Marking

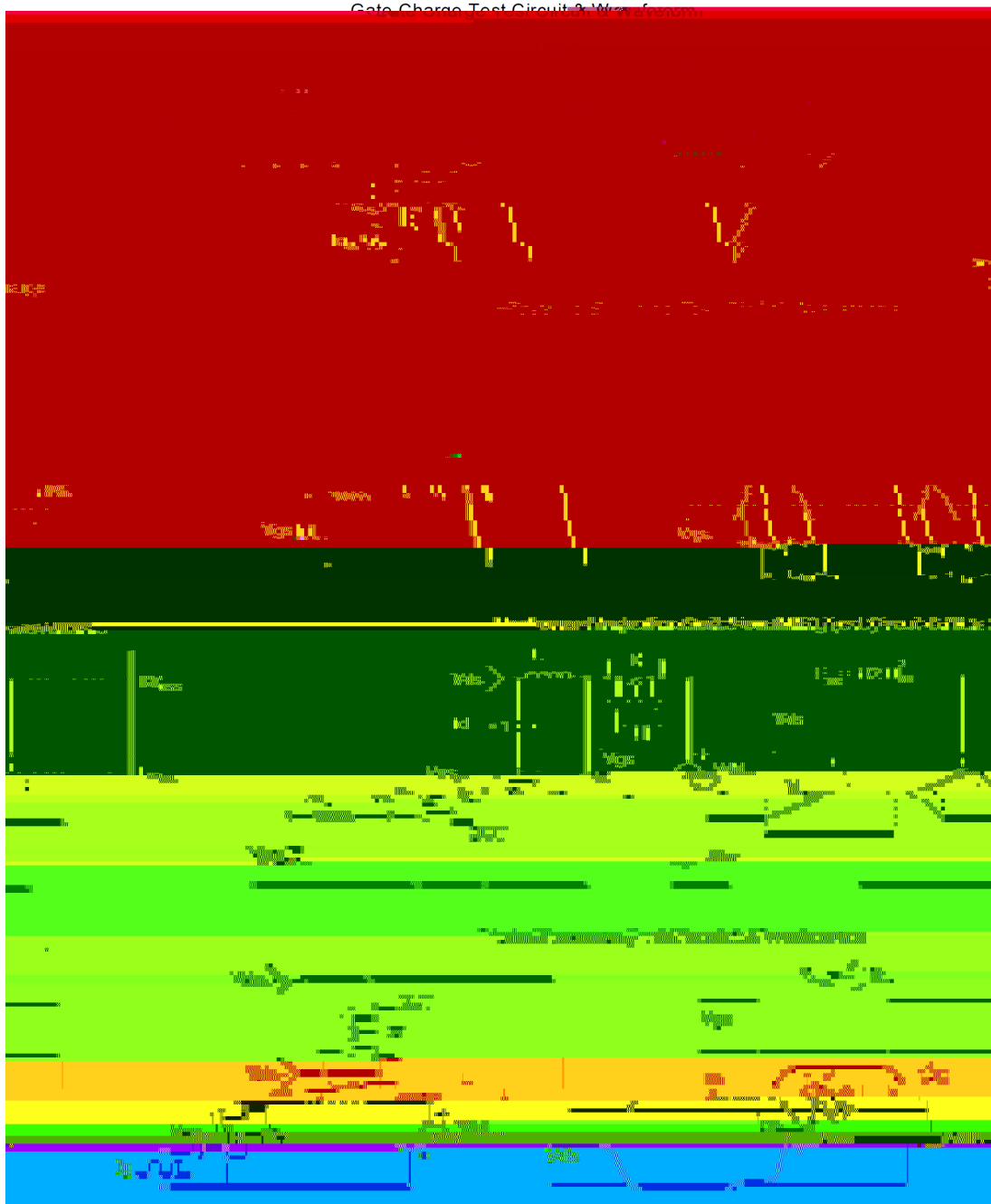
See Marking Instructions.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250 A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1.0	A
		$V_{DS}=30V$ $V_{GS}=0V$ $T_J=55$			5.0	A
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250 A$	1.5	1.9	2.5	V
On state drain current	$I_{D(on)}$	$V_{DS}=5V$ $V_{GS}=10V$	100			A
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=12A$		9.5	11.5	m
		$V_{GS}=10V$ $I_D=12A$ $T_J=125$		14	17	m
		$V_{GS}=4.5V$ $I_D=10A$		12.5	15.5	m
Forward Transconductance	g_{FS}	$V_{DS}=5.0V$ $I_D=12A$		45		S
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$		0.75	1	V
Maximum Body-Diode Continuous Current	I_S				4	A
Input Capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$		760		pF
Output Capacitance	C_{oss}			125		pF
Reverse Transfer Capacitance	C_{rss}			70		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0MHz$	0.8	1.6	2.4	
Total Gate Charge(10V)	Q_g	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=12A$		14	25	nC
Total Gate Charge(4.5V)				6.6	12	nC
Gate-Source Charge	Q_{gs}			2.4		nC
Gate-Drain Charge	Q_{gd}			3		nC
Gate-Source Charge	Q_{gs}		$V_{GS}=4.5V$ $V_{DS}=15V$ $I_D=12A$		2.4	
Gate-Drain Charge	Q_{gd}			3		nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15 V$ $V_{GS}=10V$ $R_L=1.25$ $R_{GEN}=3$		4.4		ns
Turn-On Rise Time	t_r			9		ns
Turn-Off Delay Time	$t_{d(off)}$			17		ns
Turn-Off Fall Time	t_f			6		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F=12A$ $di/dt=100A/ s$				

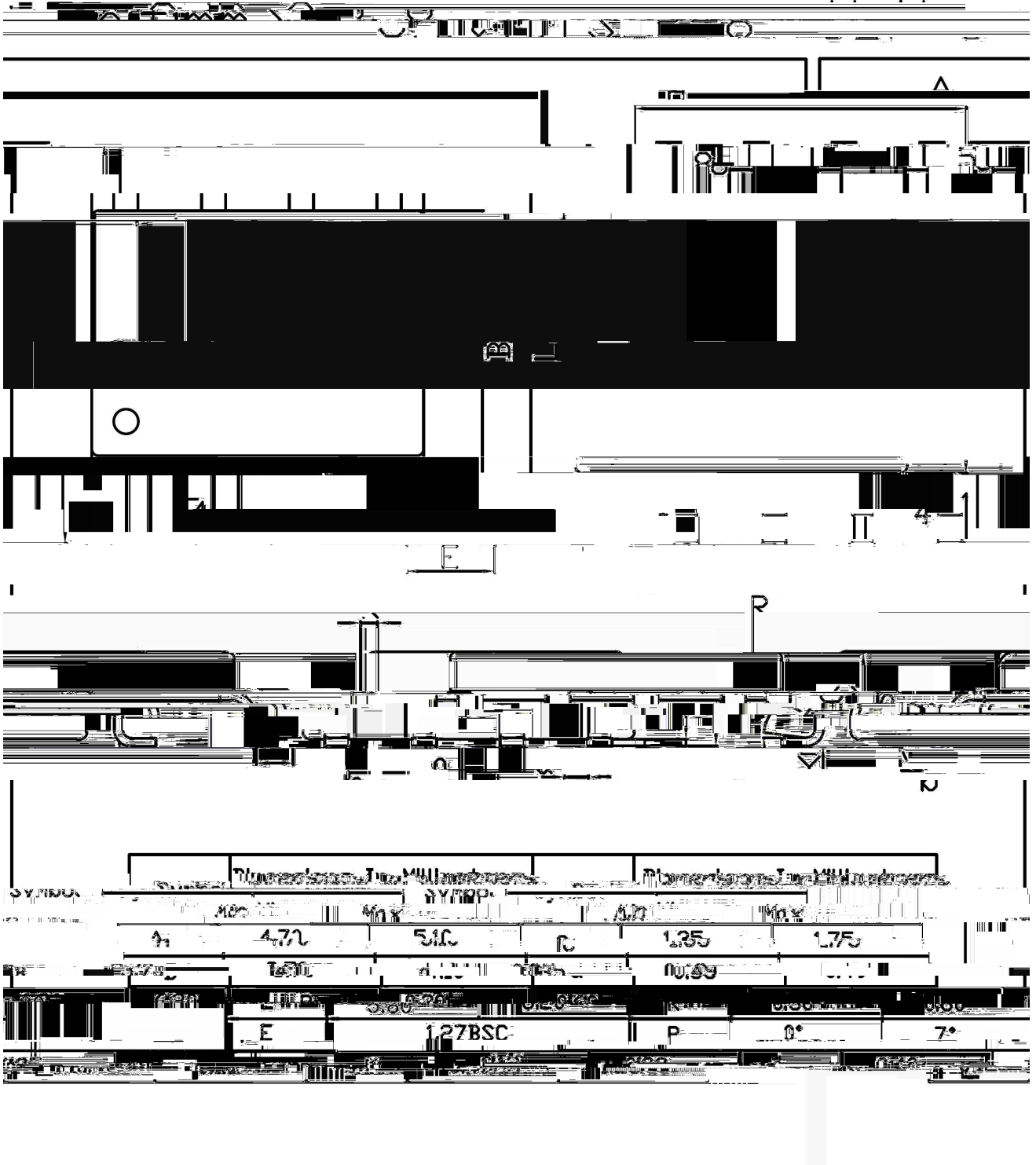
BRCS4306SC
Rev.D Feb-2019

Electrical Characteristic Curve

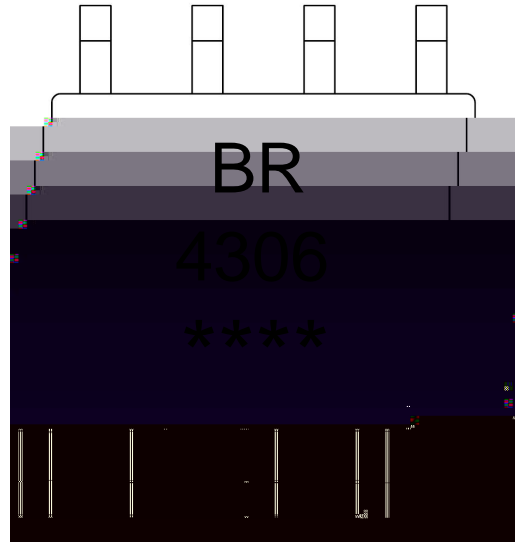




/ Package Dimensions



/ Marking Instructions



BR

4306

Note:

BR: Company Code.

4306: Product Type.

****: Lot No. Code, code change with Lot No.

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